

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising
a semiconductor substrate, a capacitor structure formed
above the semiconductor substrate and comprising
5 a first electrode, a second electrode provided below
the first electrode, a third electrode provided below
the second electrode, a first dielectric film provided
between the first electrode and the second electrode,
and a second dielectric film provided between the
10 second electrode and the third electrode, an insulating
film covering the capacitor structure and having
a first hole reaching the first electrode, a second
hole reaching the second electrode, and a third hole
reaching the third electrode, a first conductive
15 connection electrically connecting the first electrode
and the third electrode and having portions buried in
the first and third holes, and a second conductive
connection formed separately from the first conductive
connection and having a portion buried in the second
20 hole.